

Photoresponse study of MWCNTS/insulator/n-type Si/insulator/metal heterostructures as a function of the density of MWCNTs layer

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Syntesis method: Chemical Vapor Deposition





- 500 nm n-type Si (resistivity 1-5 Ωcm, doping ~10¹⁵ cm⁻³) with top and back surfaces covered by140 nm Si₃N₄
- Thermal evaporation of 3 nm Ni film
- Thermal annealing to obtain Ni nanoclusters
- Acetylene introduction and CNT growth

Electrical Characterization



External Quantum Efficiency

$$E.Q.E. = \frac{electron/sec}{photon/sec} = \frac{I_{ph}}{e} / \frac{P}{E_{\lambda}} = \frac{I_{ph} hc}{eP\lambda}$$

Experimental setup:





- Sample holder with micrometers screw gauges that allows movements along the x and y directions
- Optical fibre that form a small dot over the sample surface
- LED light: Wavelength λ =380 nm and Power P=70 μ W

Sample 1: Q.E. Map





Sample 1: Morphological analysis



Lateral border



Top and bottom border



6

Sample 2: MWCNTs film thickness reduction







Sample 2: Morphological analysis



Sample 2: Q.E. Map before remotion

Sample 2: Q.E. Map after remotion

Sample 3: Q.E. Map

Sample 3: Morphological analysis

2 remotion 1 remotion 0 remotion

Observation

Conclusions

• A better exposure of the substrate implies an higher values of the photocurrent.

• The photocurrent can be measured only when the MWCNT is illuminated, and only if the nanotubes are electrically contacted to the pads.

- The generation of the photo-charges occurs mostly in the silicon substrate. the MWCNTs film act as a barrier that reduces the number of photon that can actually reaches the substrate.
- The MWCNTs film act as a semitransparent electrode for photo-charge collection.

Thanks for the attention